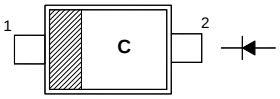
SB521WT

Silicon Epitaxial Planar Schottky Barrier Diode

for low current rectification and high speed
switching applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**C**"
Simplified outline SOD-523 and symbol

Features

• Extremely small surface mounting type

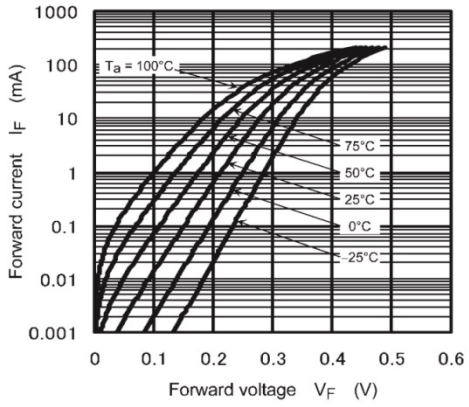
Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	200	mA
Non-repetitive Peak Forward Current	I_{FM}	300	mA
Peak Forward Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation [1)]	P_{tot}	150	mW
Junction Temperature	T_j	125	℃
Operating Temperature Range	T_{opr}	- 40 to + 100	℃
Storage Temperature Range	T_{stg}	- 55 to + 125	℃

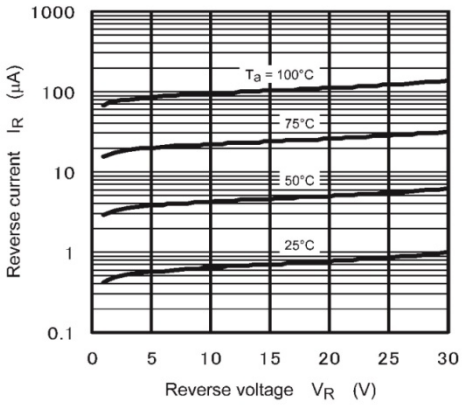
[1)] Mounted on a glass-epoxy circuit board of 20 mm X 20 mm, Pad dimension of 4 mm X 4 mm.

Characteristics at T_a = 25℃

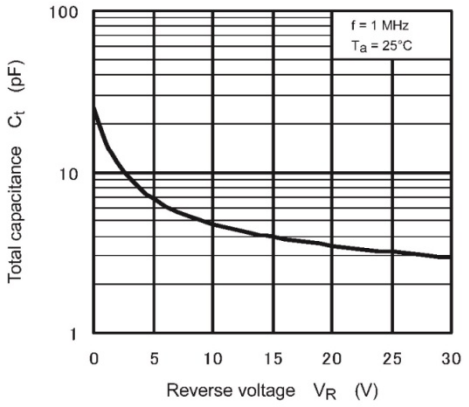
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 200 mA	V_F	-	0.5	V
Reverse Current at V_R = 10 V at V_R = 30 V	I_R	- -	20 30	µA µA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	26	-	pF



I_F - V_F



I_R - V_R



C_t - V_R

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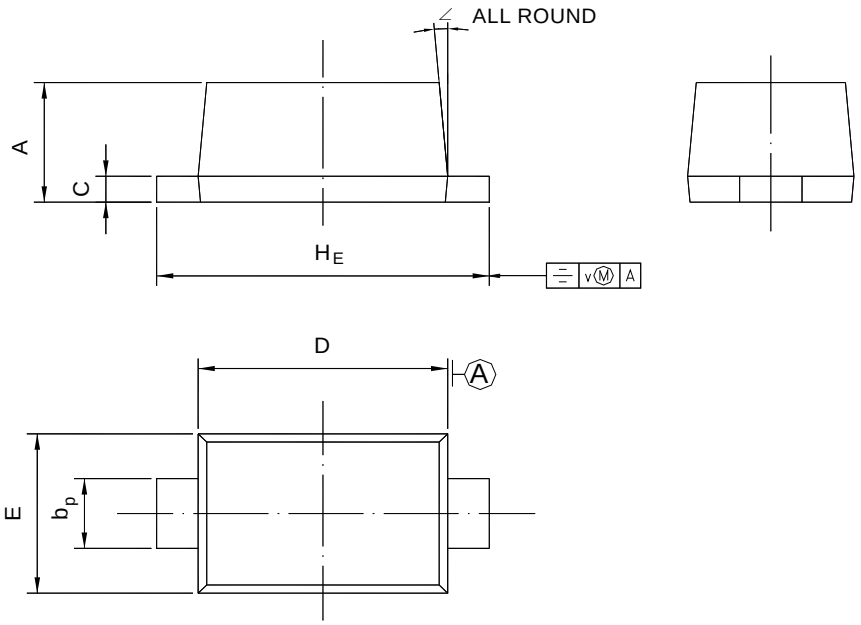
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°